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**INTEGRATED CIRCUITS, SILICON MONOLITHIC,
32-BIT ARM® CORTEX®-M7 MICROCONTROLLER**

BASED ON TYPE SAMRH707

ESCC Detail Specification No. 9512/008

Issue 1	June 2025
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DCR No.	CHANGE DESCRIPTION

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1 GENERAL

1.1 SCOPE

This specification details the ratings, physical and electrical characteristics and test and inspection data for the component type variants and/or the range of components specified below. It supplements the requirements of, and shall be read in conjunction with, the ESCC Generic Specification listed under Applicable Documents.

1.2 APPLICABLE DOCUMENTS

The following documents form part of this specification and shall be read in conjunction with it:

- (a) ESCC Generic Specification No. 9000.
- (b) MIL-STD-883, Test Method Standard for Microcircuits.

1.3 TERMS, DEFINITIONS, ABBREVIATIONS, SYMBOLS AND UNITS

For the purpose of this specification, the terms, definitions, abbreviations, symbols and units specified in ESCC Basic Specification No. 21300 shall apply.

1.4 THE ESCC COMPONENT NUMBER AND COMPONENT TYPE VARIANTS

1.4.1 The ESCC Component Number

The ESCC Component Number shall be constituted as follows:

Example: 951200x01R

- Detail Specification Reference: 951200x
- Component Type Variant Number: 01
- Total Dose Radiation Level Letter: R (as applicable)

1.4.2 Component Type Variants

The component type variants applicable to this specification are as follows:

Variant Number	Based on Type	Case	Terminal Material and Finish	Weight max g	Total Dose Radiation Level Letter (Notes 2, 3)
01	SAMRH707	CQFP-164	D2 (Note 1)	18	E [20krad(Si)] or R [100krad(Si)]

NOTES:

1. The terminal material and finish shall be in accordance with the requirements of ESCC Basic Specification No. 23500.
2. Total dose radiation level letters are defined in ESCC Basic Specification No. 22900. If an alternative radiation test level is specified in the Purchase Order the letter shall be changed accordingly.
3. The Total Dose Radiation Level Letter shall be validated as follows:
 - For letter E: Tested up to 30krad(Si) with non-volatile memory selected (i.e. in read mode)
 - For letter R: Tested up to 150krad(Si) with non-volatile memory unselected

1.5 MAXIMUM RATINGS

The maximum ratings shall not be exceeded at any time during use or storage. Functional performance for extended periods at the maximum ratings may adversely affect device reliability.

Maximum ratings shall only be exceeded during testing to the extent specified in this specification and when stipulated in the Test Methods and Procedures of the applicable ESCC generic specification.

Characteristics	Symbols	Maximum Ratings	Units	Remarks
Supply Voltage	V_{DD} V_{CC}	-0.3 to 2 -0.3 to 4	V	Notes 1, 2, 3
I/O Input Voltage Range	V_{IN}	-0.3 to 2.25	V	Note 1, 3
Operating Temperature Range	T_{op}	-55 to +125	°C	Note 1 T_{amb}
Storage Temperature Range	T_{stg}	-65 to +150	°C	
Junction Temperature	T_j	+175	°C	
Thermal Resistance, Junction-to-Case	$R_{th(j-c)}$	1	°C/W	
Soldering Temperature	T_{sol}	+345	°C	Note 4

NOTES:

- The following operating conditions also apply. Device performance beyond these operating conditions is not guaranteed:

Characteristics	Symbols	Maximum Rated Operating Conditions	Units	Remarks
Supply Voltage	V_{DD} V_{CC}	1.65 to 1.95 3 to 3.6	V	Notes 2, 3
I/O Input Voltage Range	V_{IN}	As per Maximum Ratings table		Note 3
Operating Temperature Range	T_{op}	As per Maximum Ratings table		T_{amb}

- V_{DD} is for Core and V_{CC} is for I/O.
- With reference to $V_{SS} = 0V$.
- Duration 10 seconds maximum at a distance of not less than 1.6 mm from the device body and the same terminal shall not be re-soldered until 3 minutes have elapsed.

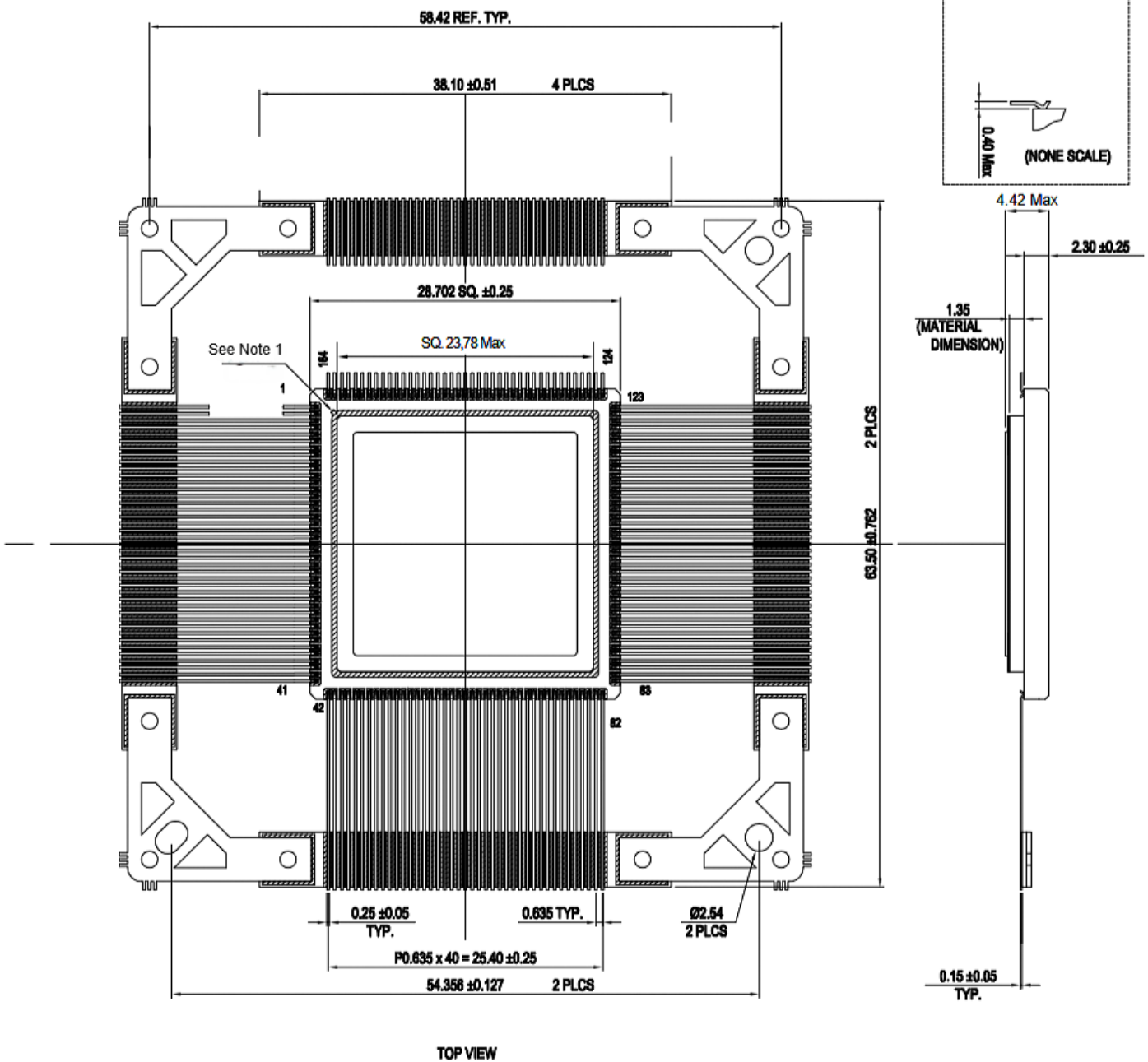
1.6 HANDLING PRECAUTIONS

These devices are susceptible to damage by electrostatic discharge. Therefore, suitable precautions shall be employed for protection during all phases of manufacture, testing, packaging, shipment and any handling.

These components are categorised as Class 1 per ESCC Basic Specification No. 23800 with a Minimum Critical Path Failure Voltage of < 250 Volts.

(Note: < 250V applies for pins PA0 to PA15 and PD28 to PD31. Other pins level is < 1000V).

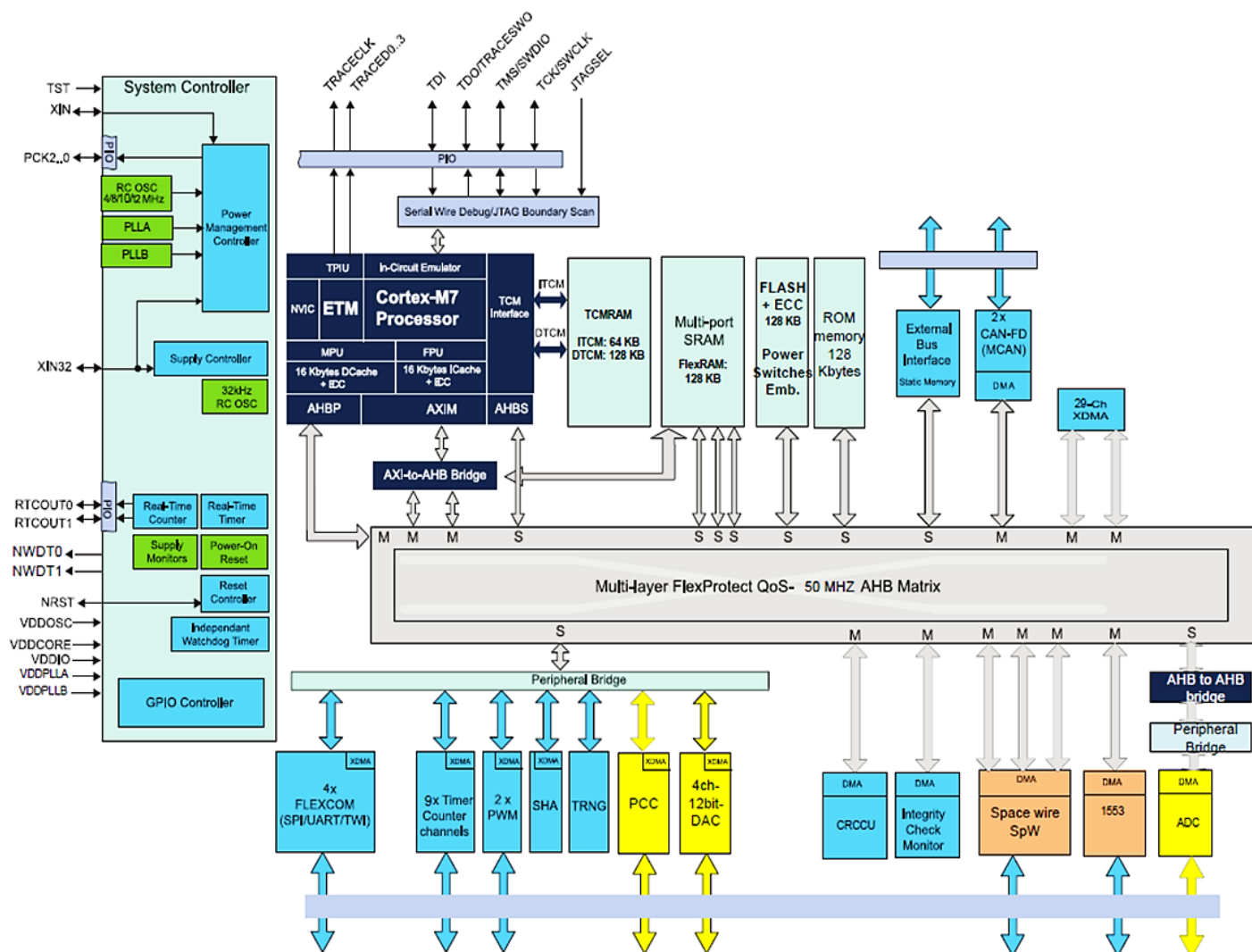
1.7 PHYSICAL DIMENSIONS AND TERMINAL IDENTIFICATION Ceramic Quad Flat Package (CQFP-164) – 164 Tied Leads



NOTES:

1. Terminal identification is specified by reference to the index mark.
2. Dimensions in mm.

1.8 FUNCTIONAL DIAGRAM

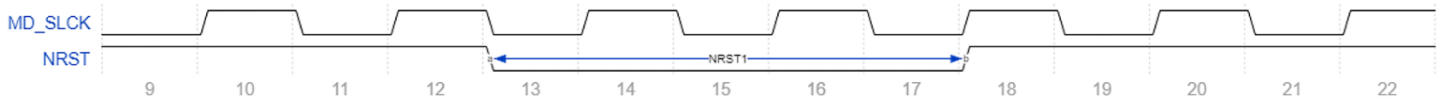


1.9 PIN ASSIGNMENT

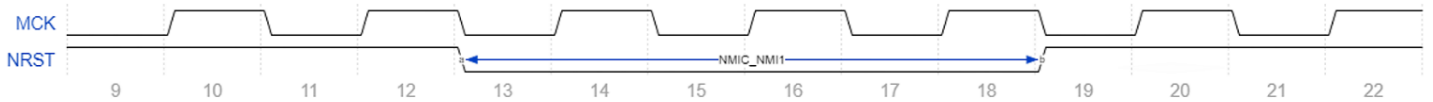
Pin	Signal	Pin	Signal	Pin	Signal	Pin	Signal
1	GND_CORE	42	GND_CORE	83	GND_CORE	124	GND_CORE
2	VDD_CORE	43	VDD_CORE	84	VDD_CORE	125	VDD_CORE
3	PA20	44	PB20	85	PC12	126	PD28
4	PA21	45	PB21	86	PC13	127	PD29
5	PA22	46	PB22	87	PC14	128	PD30
6	PA23	47	PB23	88	PC15	129	PD31
7	PA24	48	PB24	89	PC16	130	VDDIO_DAC
8	PA25	49	PB25	90	PC17	131	GNDIO_DAC
9	PA26	50	PB26	91	PC18	132	AD_DAC_GNDREF
10	PA27	51	PB27	92	PC19	133	AD_DAC_VREFIN
11	PA28	52	PB28	93	PC20	134	ANA_GND
12	PA29	53	PD0	94	PC21	135	ANA_3V3

Pin	Signal	Pin	Signal	Pin	Signal	Pin	Signal
13	PA30	54	PD1	95	PC22	136	VDDIO_ADC
14	PA31	55	PD2	96	PC23	137	GNDIO_ADC
15	PB0	56	PD3	97	PC24	138	PA0
16	PB1	57	TST	98	PC25	139	PA1
17	PB2	58	JTAGSEL	99	PC26	140	PA2
18	VDD_PLLA/B	59	NMIC_NMI	100	PC27	141	PA3
19	GND_PLLA/B	60	NRST	101	PC28	142	PA4
20	XIN	61	VDDIO	102	VDDIO	143	VDDIO
21	PB3	62	GNDIO	103	GNDIO	144	GNDIO
22	PB4	63	PD4	104	PD10	145	PA5
23	PB5	64	PD5	105	PD11	146	PA6
24	PB6	65	PD6	106	PD12	147	PA7
25	VDDIO	66	PD7	107	PD13	148	PA8
26	GNDIO	67	PC0	108	SPWREF0	149	PA9
27	PB7	68	PC1	109	PD14	150	PA10
28	PB8	69	PC2	110	PD15	151	PA11
29	PB9	70	PC3	111	PD16	152	PA12
30	PB10	71	PC4	112	PD17	153	PA13
31	PB11	72	PC5	113	PD18	154	PA14
32	PB12	73	PC6	114	PD19	155	PA15
33	PB13	74	PC7	115	PD20	156	PA16
34	PB14	75	PC8	116	PD21	157	XIN32
35	PB15	76	PC9	117	SPWREF1	158	PC29
36	PB16	77	PC10	118	PD22	159	PC30
37	PB17	78	PC11	119	PD23	160	PA17
38	PB18	79	PD8	120	PD24	161	PA18
39	PB19	80	PD9	121	PD25	162	PA19
40	VDD_CORE	81	VDD_CORE	122	VDD_CORE	163	VDD_CORE
41	GND_CORE	82	GND_CORE	123	GND_CORE	164	GND_CORE

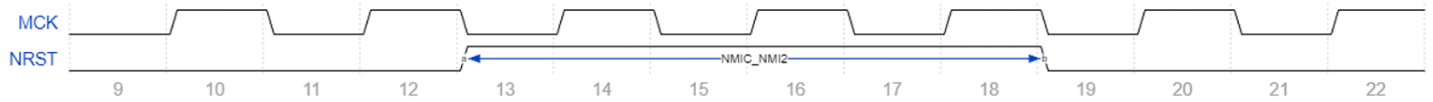
1.10 INSTRUCTION SET AND TIMING DIAGRAMS



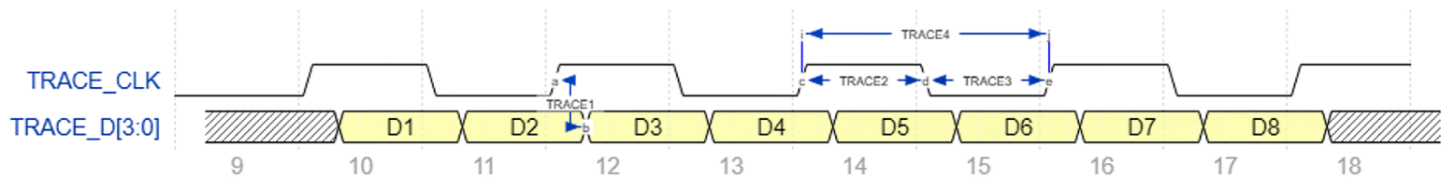
NRST Characteristics



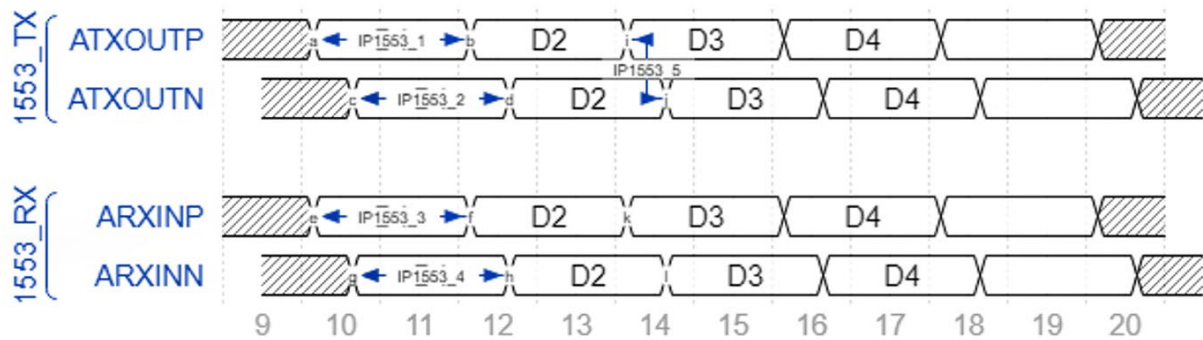
NMIC_NMI Characteristics (Active Level Low)



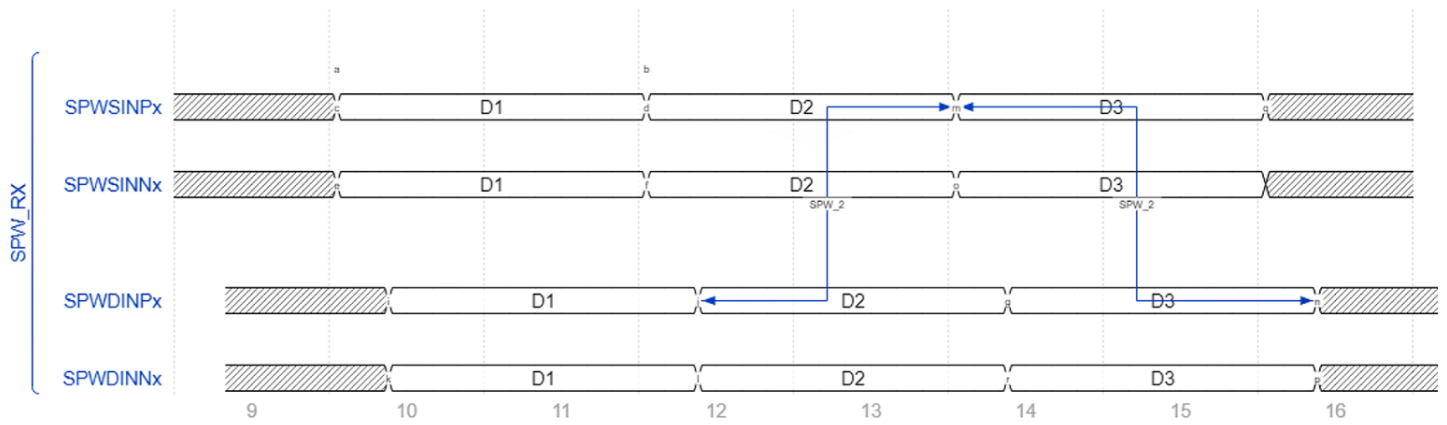
NMIC_NMI Characteristics (Active Level High)



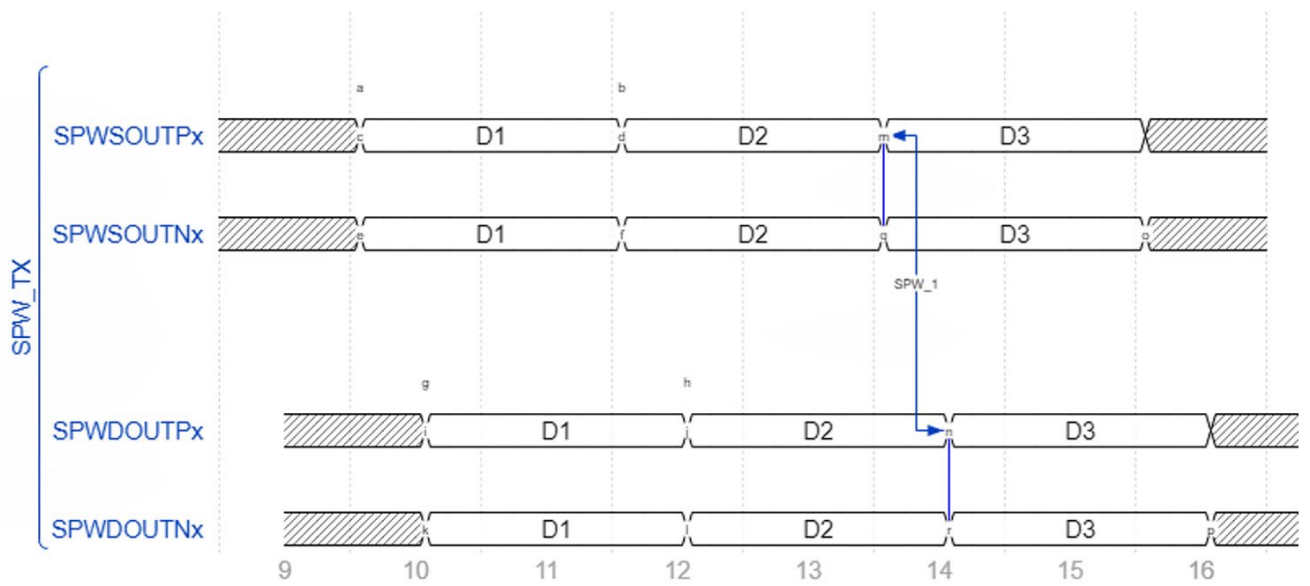
TRACE Characteristics



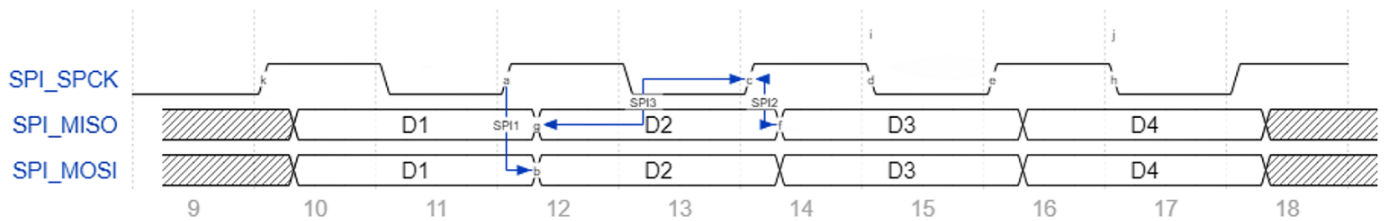
1553 Characteristics



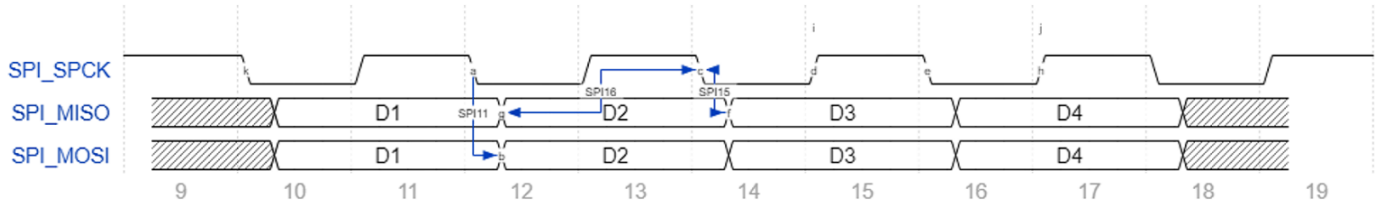
SPW RX Characteristics



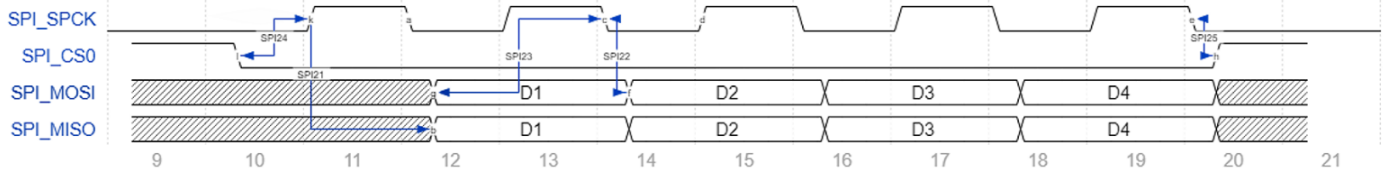
SPW TX Characteristics



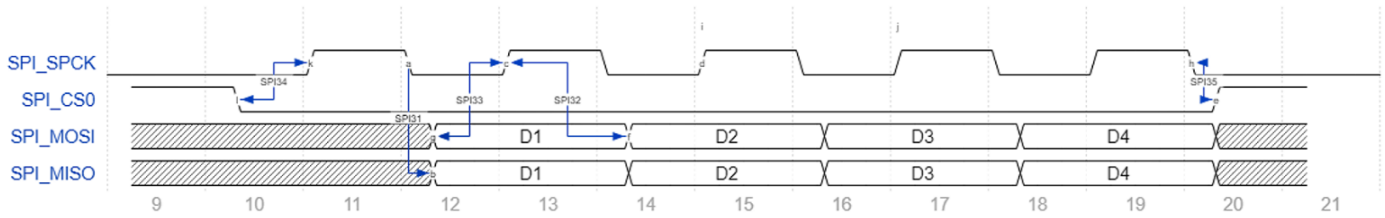
FlexCOM SPI Characteristics Master Mode (CPOL=0 and NCPHA=0) or (CPOL=1 and NCPHA=1)



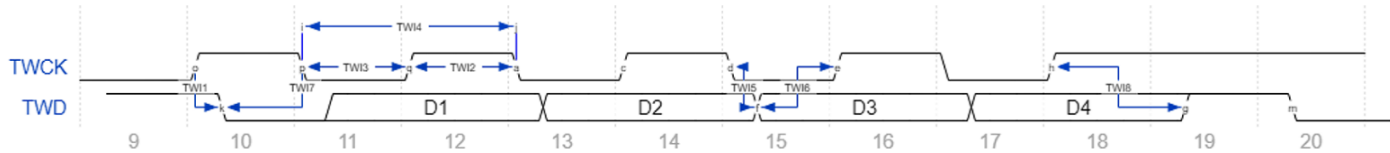
FlexCOM SPI Characteristics Master Mode (CPOL=0 and NCPHA=1) or (CPOL=1 and NCPHA=0)



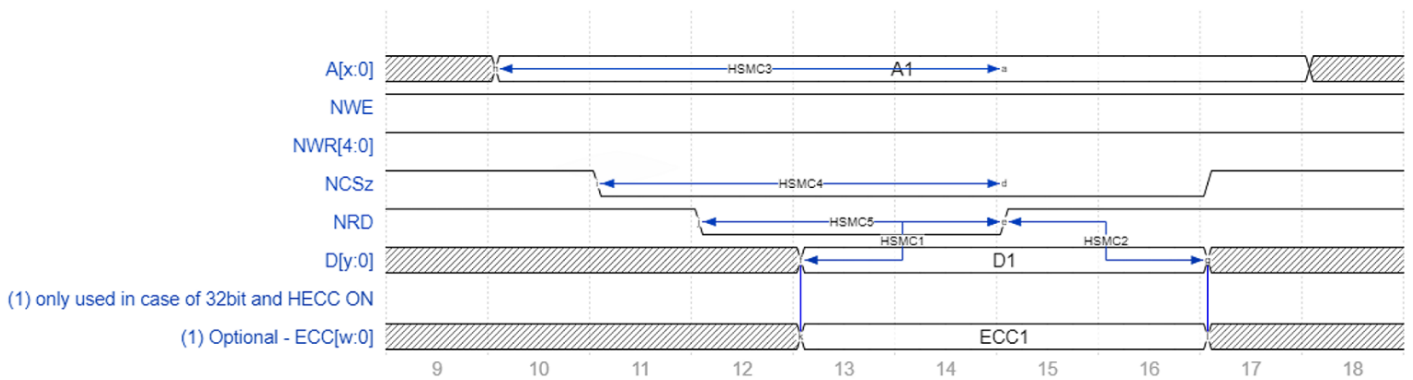
FlexCOM SPI Characteristics Slave Mode (CPOL=0 and NCPHA=0) or (CPOL=1 and NCPHA=1)



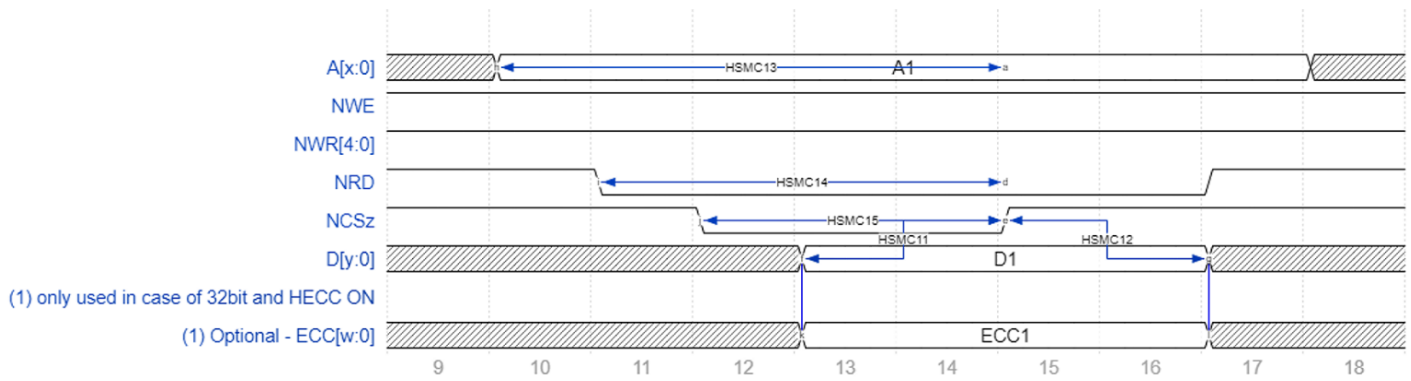
FlexCOM SPI Characteristics Slave Mode (CPOL=0 and NCPHA=1) or (CPOL=1 and NCPHA=0)



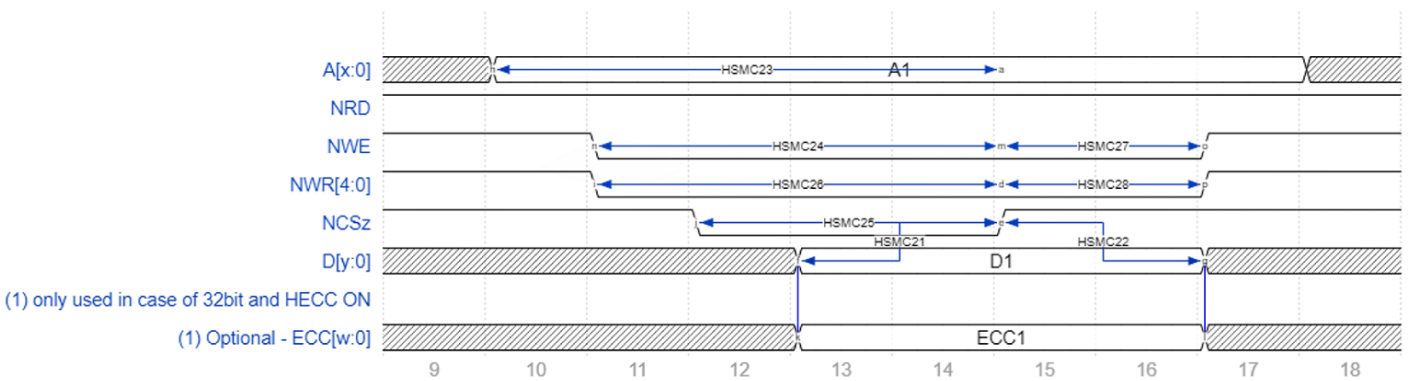
FlexCOM TWI Characteristics



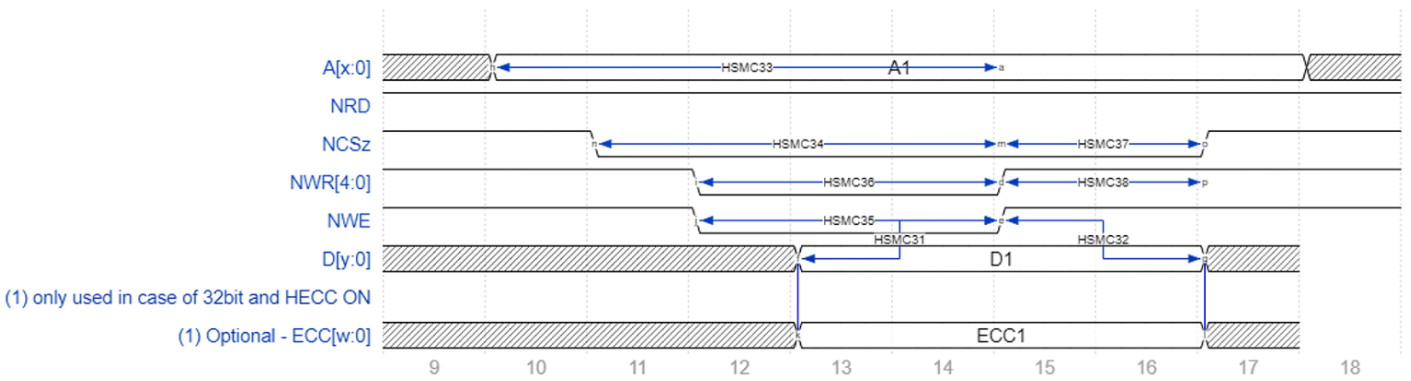
HSMC Read Data - NRD Controlled - x=[27] ; y=[31,15,7] ; z=[0:5] ; w=[11:7]



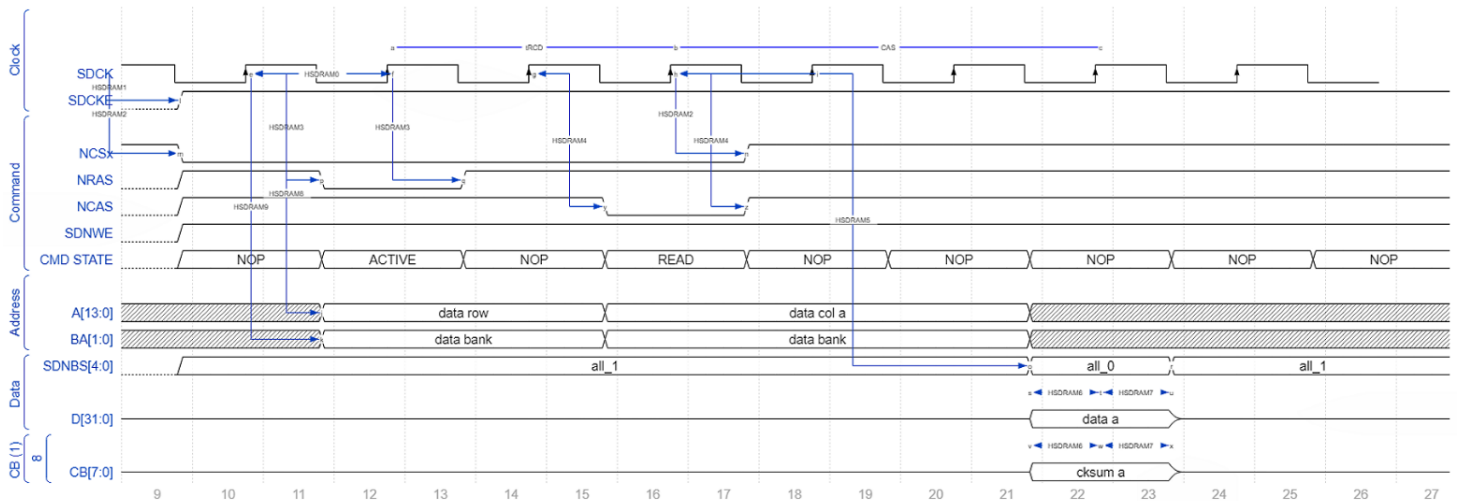
HSMC Read Data - NCS Controlled - $x=[27]$; $y=[31,15,7]$; $z=[0:5]$; $w=[11:7]$



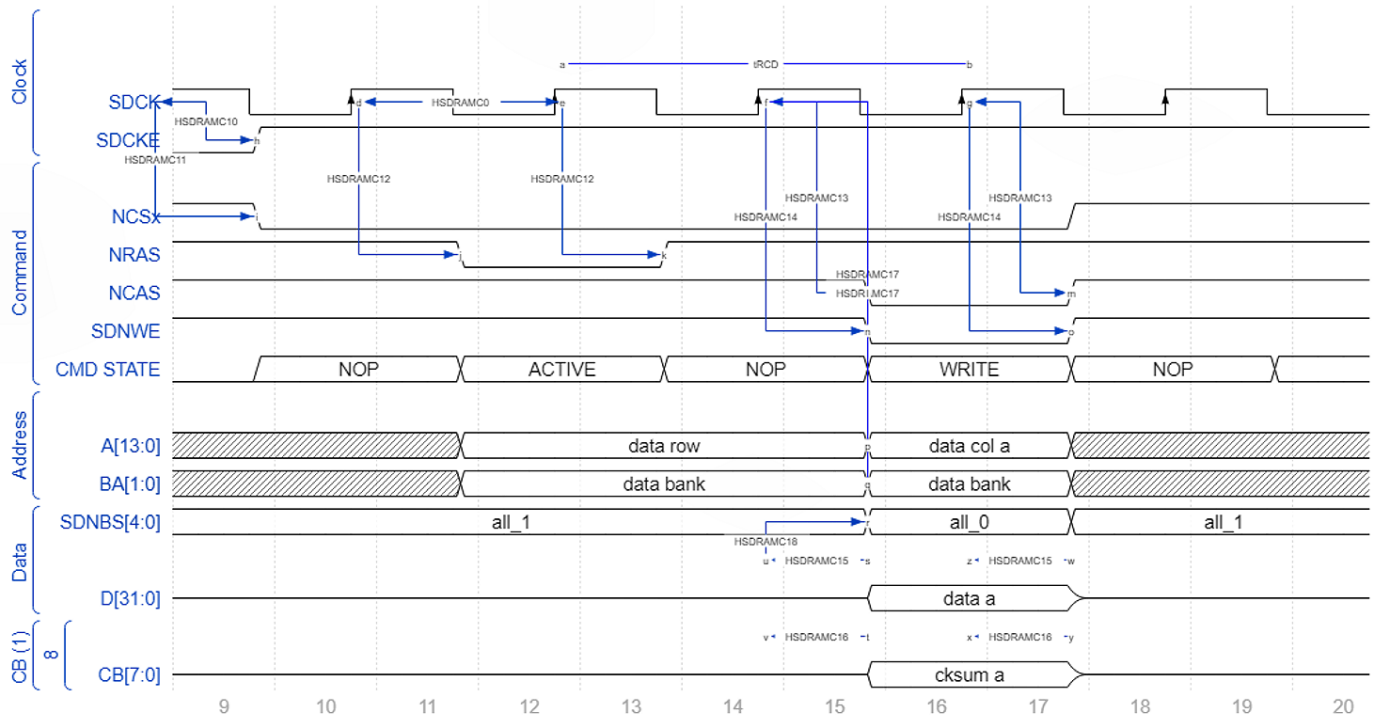
HSMC Write Data - NCS Controlled Mode - $x=[27]$; $y=[31,15,7]$; $z=[0:5]$; $w=[11:7]$



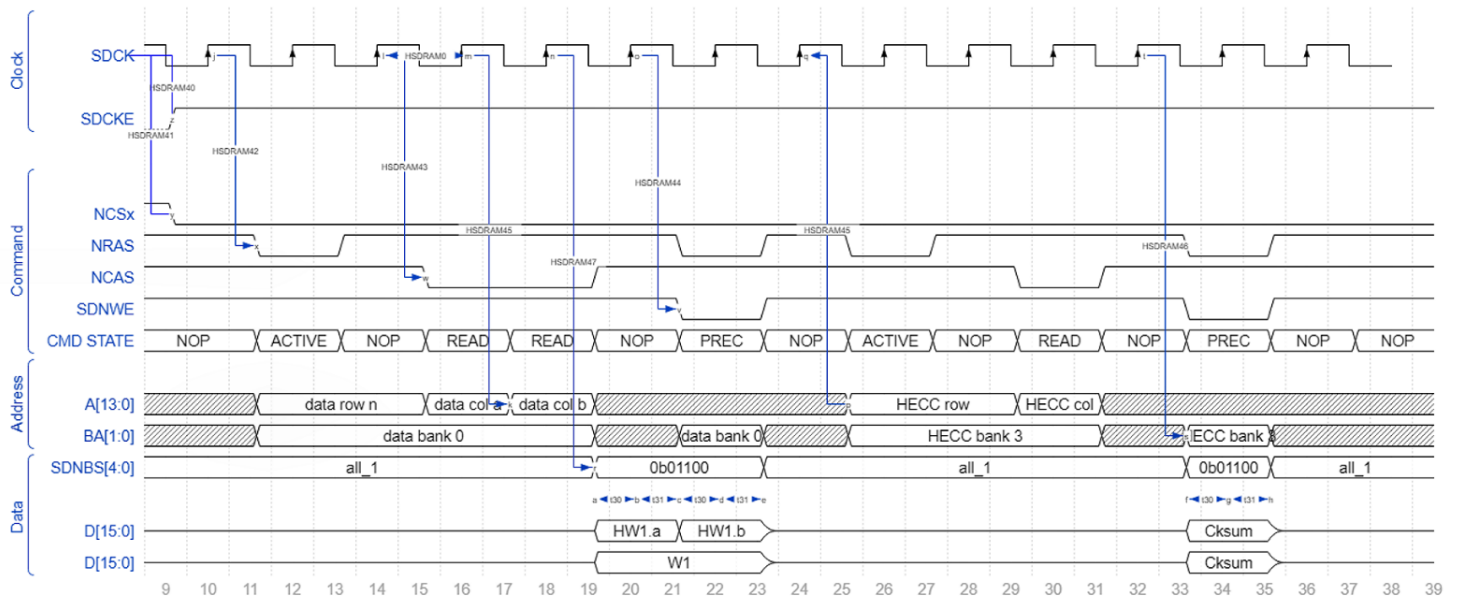
HSMC Write Data - NWE Controlled - $x=[27]$; $y=[31,15,7]$; $z=[0:5]$; $w=[11:7]$



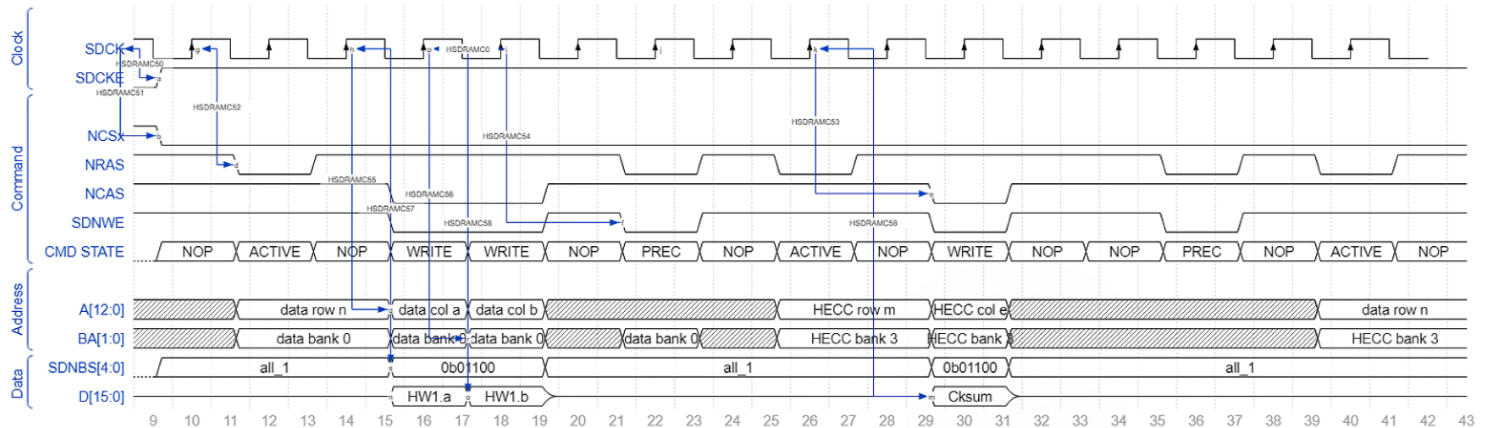
Read Word Access - 32-bit Memory - HECC ON, HECC OFF



Write Word Access - 32-bit Memory - HECC ON, HECC OFF

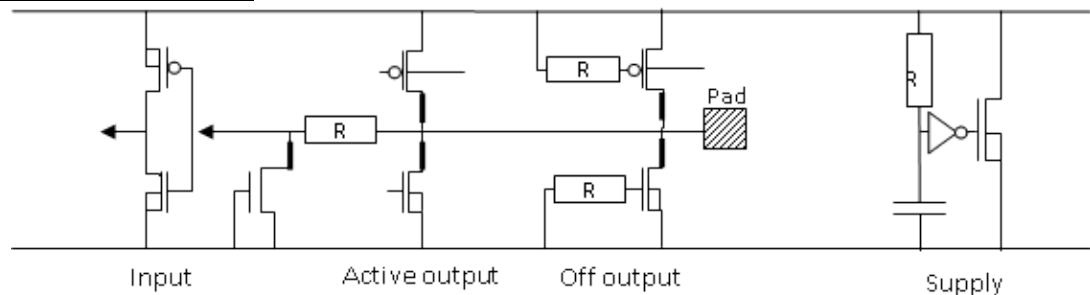


Read Word Access - 16-bit Memory - HECC ON



Write Word Access - 16-bit Memory - HECC ON

1.11 PROTECTION NETWORK



NOTES:

1. The ratio of Active Output to Off Output determines the output strength.
2. Resistors R are approximately 400Ω each.
3. Transistors with a snapback mechanism are symbolised by a bold line on the drain side.

2 REQUIREMENTS

2.1 GENERAL

The complete requirements for procurement of the components specified herein are as stated in this specification and the ESCC Generic Specification. Permitted deviations from the Generic Specification, applicable to this specification only, are listed below.

Permitted deviations from the Generic Specification and this Detail Specification, formally agreed with specific manufacturers on the basis that the alternative requirements are equivalent to the ESCC requirements and do not affect the component's reliability, are listed in the appendices attached to this specification.

2.1.1 Deviations from the Generic Specification

None.

2.2 MARKING

The marking shall be in accordance with the requirements of ESCC Basic Specification No. 21700 and as follows.

The information to be marked on the component shall be:

- (a) Terminal identification (see Para. 1.7).
- (b) The ESCC qualified components symbol (for ESCC qualified component only).
- (c) The ESCC Component Number (see Para. 1.4.1).
- (d) Traceability information.

2.3 ELECTRICAL MEASUREMENTS AT ROOM, HIGH AND LOW TEMPERATURES

Electrical measurements shall be performed at room, high and low temperatures.

2.3.1 Room Temperature Electrical Measurements

The measurements shall be performed at $T_{case} = +25(+3 -5)^{\circ}C$.

Characteristics	Symbols	MIL-STD-883 Test Method	Test Conditions $1.65V < V_{DD} < 1.95V$ $3V < V_{CC} < 3.6V$ (Note 1)	Limits		Units
				Min	Max	
Functional Tests (Min.)	-	3014	$V_{DD} = 1.65V$ $V_{CC} = 3V$ $V_{IH} = V_{DD}$ $V_{IL} = V_{SS}$	-	-	-
Functional Tests (Typ.)	-	3014	$V_{DD} = 1.8V$ $V_{CC} = 3.3V$ $V_{IH} = V_{DD}$ $V_{IL} = V_{SS}$	-	-	-
Functional Tests (Max.)	-	3014	$V_{DD} = 1.95V$ $V_{CC} = 3.6V$ $V_{IH} = V_{DD}$ $V_{IL} = V_{SS}$	-	-	-
Low Level Input Voltage	V_{IL}	-	CMOS buffers (Note 2)	-	700	mV

Characteristics	Symbols	MIL-STD-883 Test Method	Test Conditions 1.65V < V _{DD} < 1.95V 3V < V _{CC} < 3.6V (Note 1)	Limits		Units
				Min	Max	
High Level Input Voltage	V _{IH}	-	CMOS buffers (Note 2)	2	-	V
Low Level Output Voltage	V _{OL}	3007	CMOS buffers I _{OL} = 1.8, 3.6, 7.2, 14.4, 21.6 or 28.8mA depending on P-I/O's config.	-	400	mV
High Level Output Voltage	V _{OH}	3006	CMOS buffers I _{OH} = -1.8, -3.6, -7.2, -14.4, -21.6 or -28.8mA depending on P-I/O's config.	V _{CC} -0.4	-	V
Low Level Input Current 1	I _{IL1}	3009	CMOS buffers – analog V _{IN} = V _{SS}	-1	1	μA
Low Level Input Current 2	I _{IL2}	3009	CMOS buffers – digital V _{IN} = V _{SS}	-1	1	μA
Low Level Input Current with Pull-up	I _{ILPU}	3009	CMOS buffers V _{IN} = V _{SS}	-48	-18	μA
High Level Input Current 1	I _{IH1}	3010	CMOS buffers – analog V _{IN} = V _{CC} max	-1	1	μA
High Level Input Current 2	I _{IH2}	3010	CMOS buffers – digital V _{IN} = V _{CC} max	-1	1	μA
High Level Input Current with Pull-down	I _{IHPD}	3010	CMOS buffers V _{IN} = V _{CC} max	18	48	μA
ColdSparing Leakage Current	I _{CS}	3010	ColdSparing buffers V _{IN} = V _{CC} max	-1	1	μA
LVDS Differential Output Voltage	V _{OD}	3006 3007		247	454	mV
LVDS Difference of Magnitude of VOD for opposite binary state	ΔV _{OD}	3006 3007		-	50	mV
LVDS Offset Voltage	V _{OS}	3006 3007		1.125	1.375	V
LVDS Difference of Magnitude of VOS for opposite binary state	ΔV _{OS}	3006 3007		-	50	mV
Array Stand-by Current	I _{CCSBA}	3005	V _{DD} max Output = 0mA	-	20	mA
Array Operating Current	I _{CCOP}	3005	V _{DD} max V _{CC} max Coremark / frequency = 50 MHz	-	500	mA

Characteristics	Symbols	MIL-STD-883 Test Method	Test Conditions 1.65V < V _{DD} < 1.95V 3V < V _{CC} < 3.6V (Note 1)	Limits		Units
				Min	Max	
Processor Frequency	Freq	3003	TimeCoef, Cases of Coremark run in TCM or of Dhrystone run in FlexRam (Note 3)	-	1	--
Input Pin Capacitance	C _{I33}	3012	CMOS buffers (Note 4)	-	7	pF
POR						
POR Threshold	POR	3003	V _{CC} = 3.3V	1.47	1.6	V
RC Oscillators						
Operating Period RC 32kHz	t _{OSC}	3003	(Note 5)	25	42	μs
Operating Period after calibration RC 4MHz	t _{ACC4}	3003	(Notes 5, 6)	227	278	ns
Operating Period after calibration RC 8MHz	t _{ACC8}	3003	(Notes 5, 6)	113	139	ns
Operating Period after calibration RC 10MHz	t _{ACC10}	3003	(Notes 5, 6)	90	112	ns
Operating Period after calibration RC 12MHz	t _{ACC12}	3003	(Notes 5, 6)	75	93	ns
ADC						
Differential Non-linearity	ADC _{DNL}	3003	In both Single- Ended & Differential modes	-2	2	LSB
Integrated Non-linearity	ADC _{INL}	3003	In both Single- Ended & Differential modes	-4	4	LSB
Gain Error	ADC _{GE}	3003	In both Single- Ended & Differential modes	-3	3	%
Offset Error	ADC _{OE}	3003	In Single-Ended mode	-50	50	LSB
			In Differential mode	-30	30	
DAC						
Differential Non-linearity	DAC _{DNL}	3003	In Single-Ended mode	-4	4	LSB
			In Differential mode	-3	3	
Integrated Non-linearity	DAC _{INL}	3003	In Single-Ended mode	-4	4	LSB
			In Differential mode	-3	3	
Gain Error	DAC _{GE}	3003	In both Single- Ended & Differential modes	-140	140	LSB

Characteristics	Symbols	MIL-STD-883 Test Method	Test Conditions $1.65V < V_{DD} < 1.95V$ $3V < V_{CC} < 3.6V$ (Note 1)	Limits		Units
				Min	Max	
Offset Error	DAC _{OE}	3003	In Single-Ended mode In Differential mode	-75 -30	75 30	LSB

NOTES:

- Unless otherwise specified, all inputs and outputs shall be tested for each characteristic. Inputs not under test shall be $V_{IN} = V_{SS}$ or V_{CC} and outputs not under test shall be open. $V_{SS} = 0V$.
- Tested through Functional Tests.
- The maximum frequency of the Cortex-M7 processor is obtained using the following formula:

$$\text{MaxFreq} = \frac{1}{\text{TimeCoef}}$$
- Guaranteed, not tested.
- Test conditions: Tester load = 5pF, $V_{IL} = 0V$, $V_{IH} = V_{DD}$, Input signals dynamic characteristics: $t_r, t_f < 10ns$, Threshold voltages: $V_{OL} = V_{OH} = V_{DD}/2$.
- Tested only at $V_{DD} = 1.8V$. Guaranteed by Electrical Characterisation for the full V_{DD} range.

2.3.2 High and Low Temperatures Electrical Measurements

The measurements shall be performed at $T_{case} = +125 \pm 3^\circ C$ and $T_{case} = -55 \pm 3^\circ C$.

The characteristics, test methods, conditions and limits shall be the same as specified in Para. 2.3.1, Room Temperature Electrical Measurements.

2.4 PARAMETER DRIFT VALUES

Unless otherwise specified, the measurements shall be performed at $T_{case} = +25(+3 -5)^\circ C$.

The test methods and test conditions shall be as per the corresponding test defined in Para. 2.3.1, Room Temperature Electrical Measurements.

The drift values (Δ) shall not be exceeded for each characteristic specified. The corresponding absolute limit values for each characteristic shall not be exceeded.

Characteristics	Symbols	Limits			Units
		Drift Value Δ	Absolute		
			Min	Max	
Low Level Output Voltage	V _{OL}	±100	-	400	mV
High Level Output Voltage	V _{OH}	±0.1	V _{CC} -0.4	-	V
Low Level Input Current 1 and 2	I _{IL1} , I _{IL2}	±0.03	-1	1	µA
High Level Input Current 1 and 2	I _{IH1} , I _{IH2}	±0.03	-1	1	µA
ColdSparing Leakage Current	I _{CS}	±0.03	-1	1	µA
Array Stand-by Current	I _{CCSBA}	±0.75	-	50	mA

2.5 INTERMEDIATE AND END-POINT ELECTRICAL MEASUREMENTS

Unless otherwise specified, the measurements shall be performed at $T_{case} = +25(+3 -5)^{\circ}C$.

The characteristics, test methods, conditions and limits shall be the same as specified in Para. 2.3.1, Room Temperature Electrical Measurements.

2.6 POWER BURN-IN CONDITIONS

Prior to submitting the parts to Burn-In or Operating Life, a specific application is loaded in the Flash memory. This application automatically starts after the RESET is released. The correct behaviour of the device can be monitored with an on-board LED.

The specific application will run with internal PLL at 37.5MHz (75% of the maximum frequency) and will exercise the following function blocks:

1/ TCMHECC_ITCM

Description: Write and read ITCM memory

2/ TCMHECC_DTCM

Description: Write and read DTCM memory

3/ FlexRAMECC

Description: Write in FlexRAM memory with ECC enabled (Error Code Correction)

4/ TRNG

Description: Start random generator and copy data when available (interrupt)

5/ DACC_to_ADC

Description: External links between DACC (outputs) and ADC (inputs) to use single ended mode and differential mode

6/ PWM

Description: Use 2 PWM channels to output square signals

7/ RTC_to_TC

Description: External link to connect RTC output to TC input

8/ XDMAC

Description: XDMAC transfers data from FlexRAM to DTCM memory

9/ FLEXCOM_TWI

Description: External link (with pullups) between FLEXCOM1 (master) and FLEXCOM3 (slave)

10/ FLEXCOM_SPI

Description: Internal loop back (LLB) mode to check data from SPI bus

11/ FLEXCOM_USART

Description: External link to connect FLEXCOM0 to FLEXCOM2 in UART mode

12/ CAN

Description: Internal loop (LBCK) mode to check data from CAN0 to CAN1

13/ SPW

Description: External links to connect SPW0 to SPW1 (Space wire bus)

14/ ICM_FLEXRAM

Description: Use ICM (Integrity Check Monitor) to transfer data with data check using SHA

15/ IROM

Description: Read all cells of the ROM memory

16/ CRCCU

Description: Compute and compare CRC

This application program runs in loop during several minutes. Then a SCAN program starts (with a toggle coverage >70%) followed by a BIST program to activate DMA, cache and SpaceWire memories.

The activity of “application” + SCAN + BIST programs represent a toggle coverage estimate of > 70%.

Characteristics	Symbols	Test Conditions	Units
Ambient Temperature	T _{amb}	+125(+8 -0)	°C
Core Supply Voltage	V _{DD}	1.95	V
I/O Supply Voltage	V _{CC}	3.6	V
Ref. Voltage	V _{Ref}	1.25	V

NOTES:

1. Pin connections shall be as follows, where NC = Not Connected:

Pin	Signal	Loopback to Pin#	Serial Resistance	Wired To	Pin	Signal	Loopback to Pin#	Serial Resistance	Wired To
1	GND_CORE		Direct	GND	83	GND_CORE		Direct	GND
2	VDD_CORE		Direct	VDD	84	VDD_CORE		Direct	VDD
3	PA20	PD6 65	1k	Tester Pin	85	PC12			NC
4	PA21	PD9 80	1k	Tester Pin	86	PC13			NC
5	PA22	PD8 79	1k	Tester Pin	87	PC14			NC
6	PA23			NC	88	PC15			NC
7	PA24			NC	89	PC16	PA26 9	1k	Tester Pin
8	PA25		1k	Tester Pin	90	PC17	PA28 11	1k	Tester Pin
9	PA26	PC16 89	1k	Tester Pin	91	PC18			NC
10	PA27		1k	Tester Pin	92	PC19			NC
11	PA28	PC17 90	1k	Tester Pin	93	PC20		1k	Tester Pin
12	PA29		1k	Tester Pin	94	PC21		1k	Tester Pin
13	PA30		1k	Tester Pin	95	PC22		1k	Tester Pin
14	PA31			NC	96	PC23		1k	Tester Pin
15	PB0			NC	97	PC24		1k	Tester Pin
16	PB1			NC	98	PC25		1k	Tester Pin
17	PB2	PC26 99	1k	Tester Pin	99	PC26	PB2 17	1k	Tester Pin
18	VDD_PLLA/B		Direct	VDD	100	PC27		1k	Tester Pin
19	GND_PLLA/B		Direct	GND	101	PC28		1k	Tester Pin
20	XIN		10k pull up / 1k	VCC / Tester Pin	102	VDDIO		Direct	VCC
21	PB3			NC	103	GNDIO		Direct	GND
22	PB4	PB22 46	1k pull up	VCC	104	PD10	PD20 115	1k	Tester Pin
23	PB5	PB21 45	1k pull up	VCC	105	PD11	PD21 116	1k	Tester Pin
24	PB6			NC	106	PD12	PD18 113	1k	Tester Pin

Pin	Signal	Loopback to Pin#	Serial Resistance	Wired To	Pin	Signal	Loopback to Pin#	Serial Resistance	Wired To
25	VDDIO		Direct	VCC	107	PD13	PD19 114	1k	Tester Pin
26	GNDIO		Direct	GND	108	SPWREF0		direct	Vref
27	PB7			NC	109	PD14	PD24 120	1k	Tester Pin
28	PB8			NC	110	PD15	PD25 121	1k	Tester Pin
29	PB9			NC	111	PD16	PD22 118	1k	Tester Pin
30	PB10			NC	112	PD17	PD23 119	1k	Tester Pin
31	PB11		1k	Tester Pin	113	PD18	PD12 106	1k	Tester Pin
32	PB12		1k	Tester Pin	114	PD19	PD13 107	1k	Tester Pin
33	PB13			NC	115	PD20	PD10 104	1k	Tester Pin
34	PB14			NC	116	PD21	PD11 105	1k	Tester Pin
35	PB15			NC	117	SPWREF1		direct	Vref
36	PB16			NC	118	PD22	PD16 111	1k	Tester Pin
37	PB17			NC	119	PD23	PD17 112	1k	Tester Pin
38	PB18			NC	120	PD24	PD14 109	1k	Tester Pin
39	PB19			NC	121	PD25	PD15 110	1k	Tester Pin
40	VDD_CORE		Direct	VDD	122	VDD_CORE		Direct	VDD
41	GND_CORE		Direct	GND	123	GND_CORE		Direct	GND
42	GND_CORE		Direct	GND	124	GND_CORE		Direct	GND
43	VDD_CORE		Direct	VDD	125	VDD_CORE		Direct	VDD
44	PB20			NC	126	PD28	PA3 141	1k	Tester Pin
45	PB21	PB5 23	1k pull up	VCC	127	PD29	PA0 138	1k	Tester Pin
46	PB22	PB4 46	1k pull up	VCC	128	PD30	PA1 139	1k	Tester Pin
47	PB23		1k	Tester Pin	129	PD31	PA2 140	1k	Tester Pin
48	PB24		1k	Tester Pin	130	VDDIO_DAC		Direct	VCC
49	PB25			NC	131	GNDIO_DAC		Direct	GND
50	PB26			NC	132	AD_DAC_GNDREF			GND
51	PB27			NC	133	AD_DAC_VREFIN			VCC
52	PB28			NC	134	ANA_GND		Direct	GND
53	PD0			NC	135	ANA_3V3		Direct	VCC
54	PD1			NC	136	VDDIO_ADC		Direct	VCC
55	PD2			NC	137	GNDIO_ADC		Direct	GND
56	PD3			Tester Pin / Led / VDD for monitoring	138	PA0	PD29 127	1k	Tester Pin
57	TST		10k pull down / 1k	GND / Tester Pin	139	PA1	PD30 128	1k	Tester Pin
58	JTAGSEL		1k	Tester Pin	140	PA2	PD31 129	1k	Tester Pin

Pin	Signal	Loopback to Pin#	Serial Resistance	Wired To	Pin	Signal	Loopback to Pin#	Serial Resistance	Wired To
59	NMIC_NMI		1k	Tester Pin	141	PA3	PD28 126	1k	Tester Pin
60	NRST		10k pull up / 1k	VCC / Tester Pin	142	PA4		1k	Tester Pin
61	VDDIO		Direct	VCC	143	VDDIO		Direct	VCC
62	GNDIO		Direct	GND	144	GNDIO		Direct	GND
63	PD4		1k	Tester Pin	145	PA5		1k	Tester Pin
64	PD5		1k	Tester Pin	146	PA6		1k	Tester Pin
65	PD6	PA20 3	1k	Tester Pin	147	PA7		1k	Tester Pin
66	PD7		1k	Tester Pin	148	PA8		1k	Tester Pin
67	PC0			NC	149	PA9		1k	Tester Pin
68	PC1			NC	150	PA10		1k	Tester Pin
69	PC2			NC	151	PA11		1k	Tester Pin
70	PC3			NC	152	PA12		1k	Tester Pin
71	PC4		1k	Tester Pin	153	PA13		1k	Tester Pin
72	PC5		1k	Tester Pin	154	PA14		1k	Tester Pin
73	PC6			NC	155	PA15		1k	Tester Pin
74	PC7			NC	156	PA16			NC
75	PC8			NC	157	XIN32		10k pull up / 1k	VCC / Tester Pin
76	PC9			NC	158	PC29		Pull Down 10k / 1k	GND / Tester Pin
77	PC10			NC	159	PC30		Pull Down 10k / 1k	GND / Tester Pin
78	PC11			NC	160	PA17			NC
79	PD8	PA22 5	1k	Tester Pin	161	PA18			NC
80	PD9	PA21 4	1k	Tester Pin	162	PA19		1k	Tester Pin
81	VDD_CORE		Direct	VDD	163	VDD_CORE		Direct	VDD
82	GND_CORE		Direct	GND	164	GND_CORE		Direct	GND

2.7 HIGH TEMPERATURE REVERSE BIAS BURN-IN (STATIC BURN-IN) CONDITIONS

For the High Temperature Reverse Bias Burn-In, no code needs to be loaded into the Flash. The hardware remains the same as for the Power Burn-In, except for a jumper instead of a 2.2kΩ resistor on pin 28 (NRST).

2.8 OPERATING LIFE CONDITIONS

The conditions shall be as specified in Para. 2.6, Power Burn-in Conditions.

2.9 TOTAL DOSE IRRADIATION TESTING

2.9.1 Bias Conditions and Total Dose Level for Total Dose Radiation Testing

Continuous bias shall be applied during irradiation testing as specified below.

The total dose level applied shall be as specified in Para. 1.4.2 or in the Purchase Order.

Characteristics	Symbols	Test Conditions	Units
Ambient Temperature	T_{amb}	+22±3	°C
Core Supply Voltage	V_{DD}	1.95	V
I/O Supply Voltage	V_{CC}	3.6	V

NOTES:

- Pin connections shall be as follows, where NC = not connected:

Pin	Signal	Serial Resistance	Wired To	Pin	Signal	Serial Resistance	Wired To
1	GND_CORE	Direct	GND	83	GND_CORE	Direct	GND
2	VDD_CORE	Direct	VDD	84	VDD_CORE	Direct	VDD
3	PA20	2.2k	VCC	85	PC12	5.6k	VCC-GND
4	PA21	2.2k	VCC	86	PC13	5.6k	VCC-GND
5	PA22	2.2k	VCC	87	PC14	5.6k	VCC-GND
6	PA23	2.2k	VCC	88	PC15	5.6k	VCC-GND
7	PA24	2.2k	VCC	89	PC16	5.6k	VCC-GND
8	PA25	Direct	JTAG	90	PC17	5.6k	VCC-GND
9	PA26	100k	VCC	91	PC18	5.6k	VCC-GND
10	PA27	2.2k	VCC	92	PC19	5.6k	VCC-GND
11	PA28	2.2k	VCC	93	PC20	5.6k	VCC-GND
12	PA29	2.2k	VCC	94	PC21	5.6k	VCC-GND
13	PA30	2.2k	VCC	95	PC22	5.6k	VCC-GND
14	PA31	2.2k	VCC	96	PC23	5.6k	VCC-GND
15	PB0	2.2k	VCC	97	PC24	5.6k	VCC-GND
16	PB1	2.2k	VCC	98	PC25	5.6k	VCC-GND
17	PB2	2.2k	VCC	99	PC26	5.6k	VCC-GND
18	VDD_PLLA/B	Direct	VDD	100	PC27	5.6k	VCC-GND
19	GND_PLLA/B	Direct	GND	101	PC28	5.6k	VCC-GND
20	XIN	2.2k	GND	102	VDDIO	Direct	VCC
21	PB3	2.2k	VCC	103	GNDIO	Direct	GND
22	PB4	2.2k	VCC	104	PD10	2.2k	VCC
23	PB5	2.2k	VCC	105	PD11	2.2k	VCC
24	PB6	5.6k	VCC-GND	106	PD12	2.2k	VCC
25	VDDIO	Direct	VCC	107	PD13	2.2k	VCC

Pin	Signal	Serial Resistance	Wired To	Pin	Signal	Serial Resistance	Wired To
26	GNDIO	Direct	GND	108	SPWREF0	Div. Bridge	VDD
27	PB7	2.2k	VCC	109	PD14	2.2k	VCC
28	PB8	2.2k	VCC	110	PD15	2.2k	VCC
29	PB9	2.2k	VCC	111	PD16	2.2k	VCC
30	PB10	2.2k	VCC	112	PD17	2.2k	VCC
31	PB11	1k	VCC	113	PD18	2.2k	VCC
32	PB12	2.2k	VCC	114	PD19	2.2k	VCC
33	PB13	2.2k	VCC	115	PD20	2.2k	VCC
34	PB14	2.2k	VCC	116	PD21	2.2k	VCC
35	PB15	2.2k	VCC	117	SPWREF1	Div. Bridge	VDD
36	PB16	2.2k	VCC	118	PD22	2.2k	VCC
37	PB17	2.2k	VCC	119	PD23	2.2k	VCC
38	PB18	2.2k	VCC	120	PD24	2.2k	VCC
39	PB19	2.2k	VCC	121	PD25	2.2k	VCC
40	VDD_CORE	Direct	VDD	122	VDD_CORE	Direct	VDD
41	GND_CORE	Direct	GND	123	GND_CORE	Direct	GND
42	GND_CORE	Direct	GND	124	GND_CORE	Direct	GND
43	VDD_CORE	Direct	VDD	125	VDD_CORE	Direct	VDD
44	PB20	2.2k	VCC	126	PD28	2.2k	VCC
45	PB21	2.2k	VCC	127	PD29	2.2k	VCC
46	PB22	2.2k	VCC	128	PD30	2.2k	VCC
47	PB23	Direct	JTAG	129	PD31	2.2k	VCC
48	PB24	100k	VCC	130	VDDIO_DAC	Direct	VCC
49	PB25	2.2k	VCC	131	GNDIO_DAC	Direct	GND
50	PB26	2.2k	VCC	132	AD_DAC_GNDREF	Direct	GND
51	PB27	2.2k	VCC	133	AD_DAC_VREFIN	Direct	VCC
52	PB28	2.2k	VCC	134	ANA_GND	Direct	GND
53	PD0	2.2k	VCC	135	ANA_3V3	Direct	VCC
54	PD1	2.2k	VCC	136	VDDIO_ADC	Direct	VCC
55	PD2	2.2k	VCC	137	GNDIO_ADC	Direct	GND
56	PD3	2.2k	VCC	138	PA0	2.2k	VCC
57	TST	2.2k	GND	139	PA1	2.2k	VCC
58	JTAGSEL	2.2k	GND	140	PA2	2.2k	VCC
59	NMIC_NMI	2.2k	GND	141	PA3	2.2k	VCC
60	NRST	100k	(*)	142	PA4	2.2k	VCC
61	VDDIO	Direct	VCC	143	VDDIO	Direct	VCC
62	GNDIO	Direct	GND	144	GNDIO	Direct	GND

Pin	Signal	Serial Resistance	Wired To	Pin	Signal	Serial Resistance	Wired To
63	PD4	2.2k	VCC	145	PA5	2.2k	VCC
64	PD5	5.6k	VCC-GND	146	PA6	2.2k	VCC
65	PD6	5.6k	VCC-GND	147	PA7	2.2k	VCC
66	PD7	5.6k	VCC-GND	148	PA8	2.2k	VCC
67	PC0	5.6k	VCC-GND	149	PA9	2.2k	VCC
68	PC1	5.6k	VCC-GND	150	PA10	2.2k	VCC
69	PC2	5.6k	VCC-GND	151	PA11	2.2k	VCC
70	PC3	5.6k	VCC-GND	152	PA12	2.2k	VCC
71	PC4	5.6k	VCC-GND	153	PA13	2.2k	VCC
72	PC5	5.6k	VCC-GND	154	PA14	2.2k	VCC
73	PC6	5.6k	VCC-GND	155	PA15	2.2k	VCC
74	PC7	5.6k	VCC-GND	156	PA16	2.2k	VCC
75	PC8	5.6k	VCC-GND	157	XIN32	2.2k	GND
76	PC9	5.6k	VCC-GND	158	PC29	2.2k	GND
77	PC10	5.6k	VCC-GND	159	PC30	2.2k	GND
78	PC11	5.6k	VCC-GND	160	PA17	2.2k	VCC
79	PD8	2.2k	GND	161	PA18	2.2k	VCC
80	PD9	2.2k	VCC	162	PA19	2.2k	VCC
81	VDD_CORE	Direct	VDD	163	VDD_CORE	Direct	VDD
82	GND_CORE	Direct	GND	164	GND_CORE	Direct	GND

*N.B. – to release the RESET, a switch is used on pin 60 (NRST) to connect from GND to V_{CC}.

2.9.2 Electrical Measurements for Total Dose Radiation Testing

Prior to, during and on completion of irradiation testing the devices shall have successfully met the Room Temperature Electrical Measurements specified in Para. 2.3.1.

Unless otherwise stated the measurements shall be performed at T_{case} = +25(+3 -5)°C.

The characteristics, test methods, conditions and limits shall be as per the corresponding test defined in Para. 2.3.1, Room Temperature Electrical Measurements.